

MICROSTRIP/STRIPLINE NIP DIODE SWITCH

DESCRIPTION:

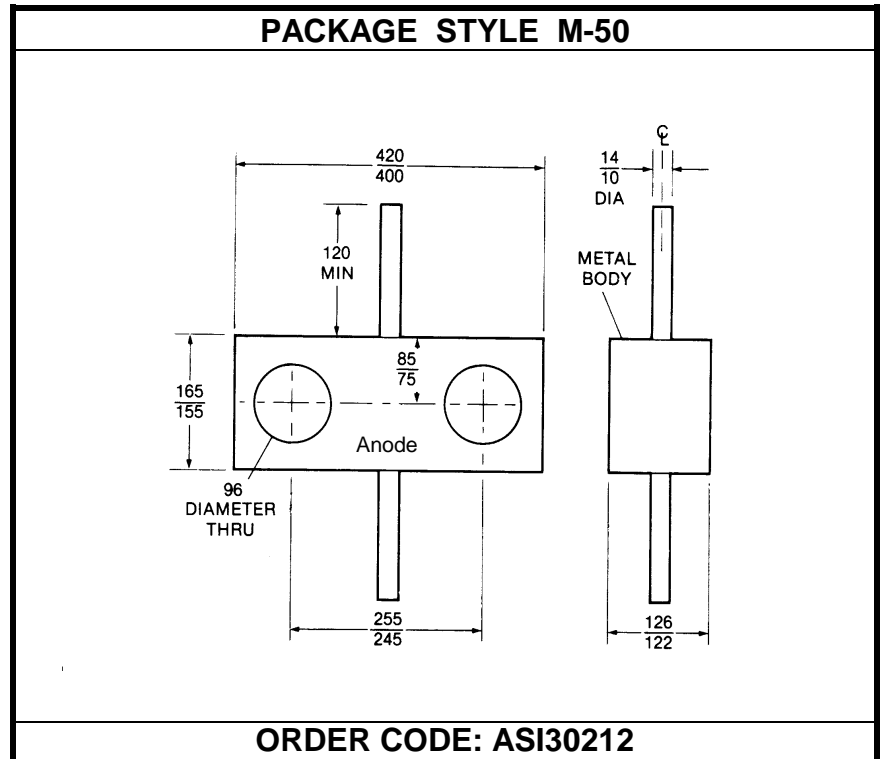
The **ASI 5082-3140** is a Silicon NIP Diode Module Designed for Reflective Attenuator and Switching Applications from 1 GHz to 18 GHz.

FEATURES INCLUDE:

- Direct replacement for **HP 5082-3140**
- Isolation = 20 dB min. at 10 GHz
- Hermetic Package

MAXIMUM RATINGS

I_F	250 mA
V_R	150 V
P_{DISS}	1.75 W @ $T_C = 25\text{ }^\circ\text{C}$
T_J	-65 $^\circ\text{C}$ to +150 $^\circ\text{C}$
T_{STG}	-65 $^\circ\text{C}$ to +150 $^\circ\text{C}$
θ_{JC}	72 $^\circ\text{C/W}$


CHARACTERISTICS $T_C = 25\text{ }^\circ\text{C}$

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
V_{BR}	$I_R = 10\text{ }\mu\text{A}$			150			V
V_F	$I_F = 100\text{ mA}$					1.0	V
τ	$I_F = 50\text{ mA}$	$I_R = 250\text{ mA}$			400		μS
I_L	$I_F = 0\text{ mA}$	$P_{IN} = 0\text{ dBm}$	$f = 10\text{ GHz}$			0.5	dB
I_L	$I_F = 100\text{ mA}$	$P_{IN} = 0\text{ dBm}$	$f = 10\text{ GHz}$	20			dB
V_{SWR}	$I_F = 0\text{ mA}$	$P_{IN} = 0\text{ dBm}$	$f = 10\text{ GHz}$			1.5:1	---